查询MRF572供应商 捷多邦，专业PCB打样工厂，24小时加急出货



# SILICON NPN RF TRANSISTOR

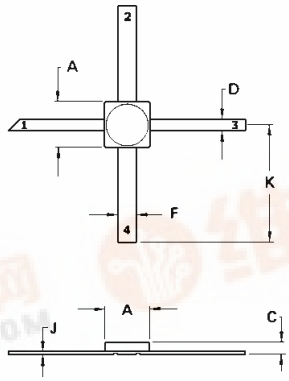
## DESCRIPTION:

The **MRF572** is Designed for Low Noise General Purpose VHF,UHF Amplifier and Oscillator Applications.

## MAXIMUM RATINGS

| | |
|---|---|
| $I_C$ | 60 mA |
| $V_{CE}$ | 12 V |
| $P_{DISS}$ | 500 mW @ $T_C$ = 25 °C |
| $T_J$ | -65 °C to +200 °C |
| $T_{STG}$ | -65 °C to +200 °C |

## PACKAGE STYLE 100MIL CERAMIC STRIPLINE




| DIM | MILLIMETERS MIN | MILLIMETERS MAX | INCHES MIN | INCHES MAX |
|---|---|---|---|---|
| A | 2.29 | 2.67 | 0.090 | 0.105 |
| C | 0.89 | 1.40 | 0.035 | 0.055 |
| D | 0.41 | 0.61 | 0.016 | 0.024 |
| F | 0.89 | 1.09 | 0.035 | 0.043 |
| J | 0.08 | 0.15 | 0.003 | 0.006 |
| K | 4.45 | 5.84 | 0.175 | 0.230 |

1 = Collector 2 & 4 = Emitter
3 = Base

## CHARACTERISTICS $T_C$ = 25 °C

| SYMBOL | TEST CONDITIONS | | | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|---|---|---|---|---|---|---|---|
| $BV_{CEO}$ | $I_C$ = 1.0 mA | | | 12 | | | V |
| $BV_{CBO}$ | $I_C$ = 100 µA | | | 20 | | | V |
| $I_{CBO}$ | $V_{CB}$ = 8.0 V | | | | | 200 | µA |
| $BV_{EBO}$ | $I_E$ = 50 µA | | | 1.5 | | | V |
| $h_{FE}$ | $V_{CE}$ = 8.0 V | $I_C$ = 10 mA | | 30 | | 300 | --- |
| $C_{cb}$ | $V_{CB}$ = 8.0 V | | f = 1.0 MHz | | 0.25 | | pF |
| $f_t$ | $V_{CE}$ = 8.0 V | $I_C$ = 25 mA | f = 1.0 GHz | | 8.0 | | GHz |
| $\|S21E\|^2$ | $V_{CE}$ = 8.0 V | $I_C$ = 25 mA | f = 1.0 GHz<br>f = 2.0 GHz | | 16.9<br>12.0 | | dB |
| GNF | $V_{CE}$ = 8.0 V | $I_C$ = 0 mA | f = 0.5 GHz<br>f = 1.0 GHz<br>f = 2.0 GHz | <br><br>10 | 16.5<br>12 | | dB |
| NF | $V_{CE}$ = 8.0 V | $I_C$ = 0 mA | f = 0.5 GHz<br>f = 1.0 GHz<br>f = 2.0 GHz | | 1.0<br>1.5<br>2.5 | 2.0 | dB |

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